

MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

Digital Transistors (BRT) R1 = 10 kΩ, R2 = 47 kΩ

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias resistor network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current - Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	6	Vdc

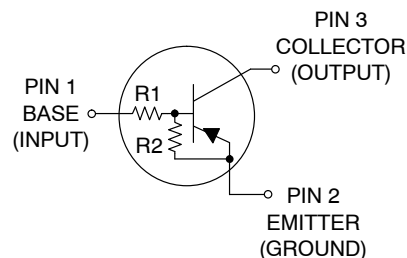
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



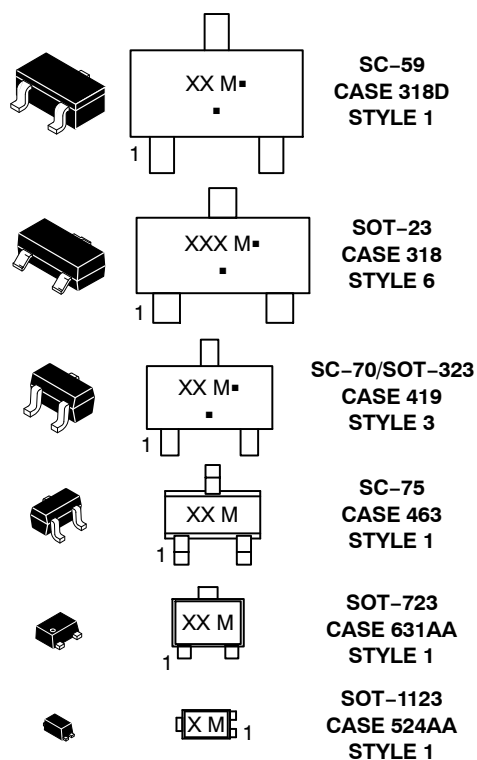
ON Semiconductor®

<http://onsemi.com>

PIN CONNECTIONS



MARKING DIAGRAMS



XXX = Specific Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping†
MUN2114T1G, SMUN2114T1G	6D	SC-59	3,000 / Tape & Reel
MMUN2114LT1G, SMMUN2114LT1G	A6D	SOT-23	3,000 / Tape & Reel
MMUN2114LT3G	A6D	SOT-23	10,000 / Tape & Reel
MUN5114T1G, SMUN5114T1G	6D	SC-70/SOT-323	3,000 / Tape & Reel
SMUN5114T3G	6D	SC-70/SOT-323	10,000 / Tape & Reel
DTA114YET1G, SDTA114YET1G	6D	SC-75	3,000 / Tape & Reel
DTA114YM3T5G	6D	SOT-723	8,000 / Tape & Reel
NSBA114YF3T5G	K	SOT-1123	8,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Figure 1. Derating Curve

MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2114)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	230	mW
Derate above 25°C		338	$\text{mW}/^\circ\text{C}$
		1.8	
		2.7	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	540	$^\circ\text{C}/\text{W}$
		370	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	264	$^\circ\text{C}/\text{W}$
		287	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS (SOT-23) (MMUN2114L)

Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	246	mW
Derate above 25°C		400	$\text{mW}/^\circ\text{C}$
		2.0	
		3.2	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	508	$^\circ\text{C}/\text{W}$
		311	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	174	$^\circ\text{C}/\text{W}$
		208	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5114)

Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	202	mW
Derate above 25°C		310	$\text{mW}/^\circ\text{C}$
		1.6	
		2.5	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	618	$^\circ\text{C}/\text{W}$
		403	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	280	$^\circ\text{C}/\text{W}$
		332	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS (SC-75) (DTA114YE)

Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	200	mW
Derate above 25°C		300	$\text{mW}/^\circ\text{C}$
		1.6	
		2.4	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	600	$^\circ\text{C}/\text{W}$
		400	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS (SOT-723) (DTA114YM3)

Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	260	mW
Derate above 25°C		600	$\text{mW}/^\circ\text{C}$
		2.0	
		4.8	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	480	$^\circ\text{C}/\text{W}$
		205	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
- FR-4 @ 500 mm², 1 oz. copper traces, still air.

MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBA114YF3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	P_D 254 297 2.0 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{\theta JA}$ 493 421	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead	(Note 3)	$R_{\theta JL}$ 193	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
- FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$)	I_{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$)	I_{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}, I_C = 0$)	I_{EBO}	-	-	0.2	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 5) ($I_C = 2.0\text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) ($I_C = 5.0\text{ mA}, V_{CE} = 10\text{ V}$)	h_{FE}	80	140	-	
Collector - Emitter Saturation Voltage (Note 5) ($I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$)	$V_{CE(sat)}$	-	-	0.25	Vdc
Input Voltage (off) ($V_{CE} = 5.0\text{ V}, I_C = 100\ \mu\text{A}$)	$V_{i(off)}$	-	0.7	-	Vdc
Input Voltage (on) ($V_{CE} = 0.2\text{ V}, I_C = 1.0\text{ mA}$)	$V_{i(on)}$	-	0.9	-	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OL}	-	-	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	-	-	Vdc
Input Resistor	R1	7.0	10	13	k Ω
Resistor Ratio	R_1/R_2	0.17	0.21	0.25	

- Pulsed Condition: Pulse Width = 300 msec, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS
MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3



Figure 2. $V_{CE(sat)}$ vs. I_C



Figure 3. DC Current Gain



Figure 4. Output Capacitance



Figure 5. Output Current vs. Input Voltage



Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS
NSBA114YF3



Figure 7. $V_{CE(sat)}$ vs. I_C

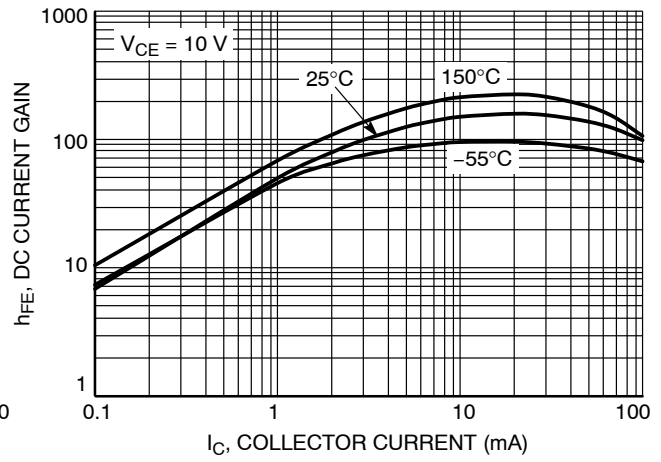


Figure 8. DC Current Gain



Figure 9. Output Capacitance



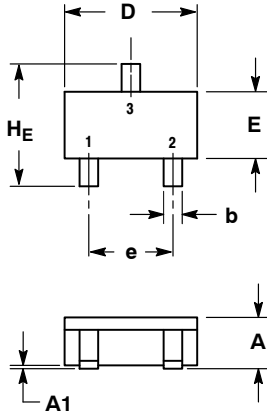
Figure 10. Output Current vs. Input Voltage



Figure 11. Input Voltage vs. Output Current

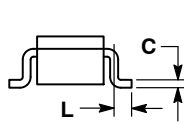
PACKAGE DIMENSIONS

SC-59
CASE 318D-04
ISSUE H



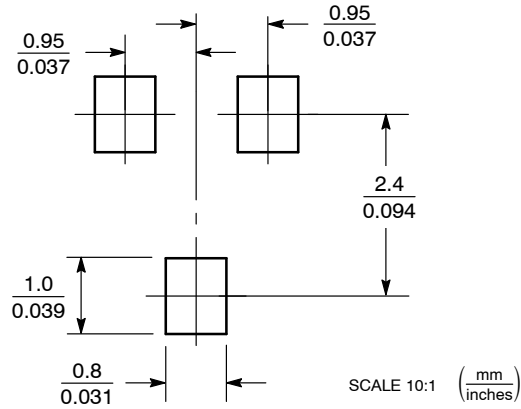
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118



- STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

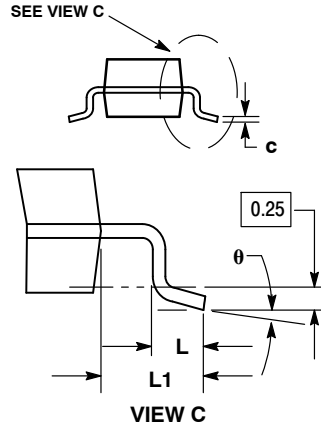
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP

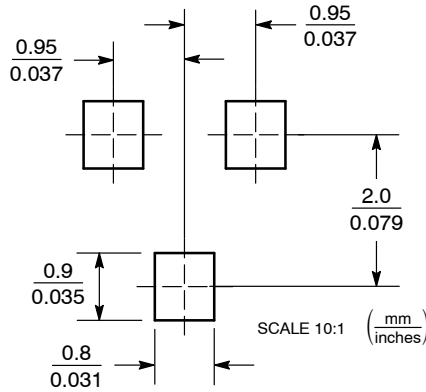


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SC-70 (SOT-323)
CASE 419-04
ISSUE N

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3:
PIN 1: BASE
2: EMITTER
3: COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

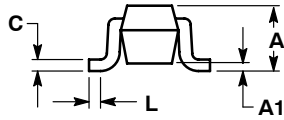
PACKAGE DIMENSIONS

SC-75/SOT-416
CASE 463
ISSUE F



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
H _E	1.50	1.60	1.70	0.061	0.063	0.065



- STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



SCALE 10:1 ($\frac{\text{mm}}{\text{inches}}$)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-723
CASE 631AA
ISSUE D



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H _E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

- STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED
SOLDERING FOOTPRINT*



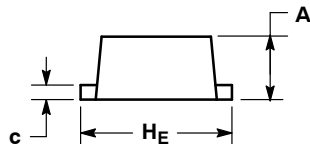
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

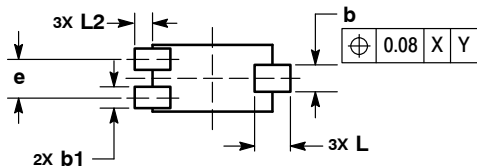
SOT-1123
CASE 524AA
ISSUE C



TOP VIEW



SIDE VIEW



BOTTOM VIEW

NOTES:

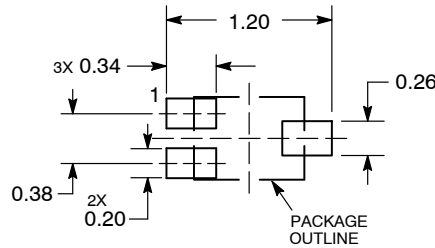
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS		
DIM	MIN	MAX
A	0.34	0.40
b	0.15	0.28
b1	0.10	0.20
c	0.07	0.17
D	0.75	0.85
E	0.55	0.65
e	0.35	0.40
HE	0.95	1.05
L	0.185	REF
L2	0.05	0.15

STYLE 1:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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